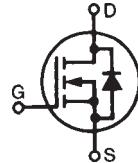


PolarHT™ Power MOSFET

IXTQ 120N15P
IXTT 120N15P

V_{DSS} = 150 V
I_{D25} = 120 A
R_{DS(on)} ≤ 16 mΩ

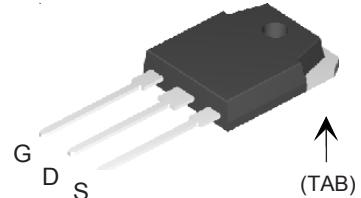
N-Channel Enhancement Mode
Avalanche Rated



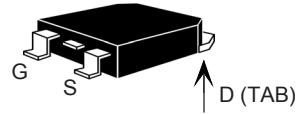
Symbol	Test Conditions	Maximum Ratings		
V _{DSS}	T _J = 25°C to 175°C	150	V	
V _{DGR}	T _J = 25°C to 175°C; R _{GS} = 1 MΩ	150	V	
V _{DSS}	Continuous	±20	V	
V _{GSM}	Transient	±30	V	
I _{D25}	T _C = 25°C	120	A	
I _{D(RMS)}	External lead current limit	75	A	
I _{DM}	T _C = 25°C, pulse width limited by T _{JM}	260	A	
I _{AR}	T _C = 25°C	60	A	
E _{AR}	T _C = 25°C	60	mJ	
E _{AS}	T _C = 25°C	2.0	J	
dv/dt	I _S ≤ I _{DM} , di/dt ≤ 100 A/μs, V _{DD} ≤ V _{DSS} , T _J ≤ 150°C, R _G = 4 Ω	10	V/ns	
P _D	T _C = 25°C	600	W	
T _J		-55 ... +175	°C	
T _{JM}		175	°C	
T _{stg}		-55 ... +150	°C	
T _L	1.6 mm (0.062 in.) from case for 10 s	300	°C	
T _{SOLD}	Plastic body for 10 s	260	°C	
M _d	Mounting torque (TO-3P)	1.13/10	Nm/lb.in.	
Weight	TO-3P TO-268	5.5 5.0	g g	

Symbol	Test Conditions (T _J = 25°C, unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
BV _{DSS}	V _{GS} = 0 V, I _D = 250 μA	150		V
V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	3.0		V
I _{GSS}	V _{GS} = ±20 V _{DC} , V _{DS} = 0		±100	nA
I _{DSS}	V _{DS} = V _{DSS} V _{GS} = 0 V		25 500	μA
R _{DS(on)}	V _{GS} = 10 V, I _D = 0.5 I _{D25} Pulse test, t ≤ 300 μs, duty cycle d ≤ 2 %		16	mΩ

TO-3P (IXTQ)



TO-268 (IXTT)



G = Gate D = Drain
S = Source TAB = Drain

Features

- International standard packages
- Unclamped Inductive Switching (UIS) rated
- Low package inductance
 - easy to drive and to protect

Advantages

- Easy to mount
- Space savings
- High power density

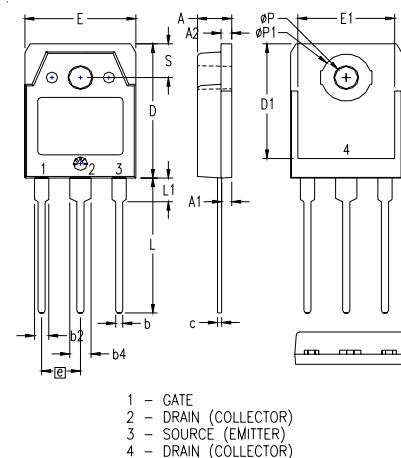
Symbol	Test Conditions	Characteristic Values		
		Min.	Typ.	Max.
g_{fs}	$V_{DS} = 10 \text{ V}$; $I_D = 0.5 I_{D25}$, pulse test	40	60	S
C_{iss} C_{oss} C_{rss}	$V_{GS} = 0 \text{ V}$, $V_{DS} = 25 \text{ V}$, $f = 1 \text{ MHz}$	4900	pF	
		1300	pF	
		330	pF	
$t_{d(on)}$ t_r $t_{d(off)}$ t_f	$V_{GS} = 10 \text{ V}$, $V_{DS} = 0.5 V_{DSS}$, $I_D = 60 \text{ A}$ $R_G = 4 \Omega$ (External)	33	ns	
		42	ns	
		85	ns	
		26	ns	
$Q_{g(on)}$ Q_{gs} Q_{gd}	$V_{GS} = 10 \text{ V}$, $V_{DS} = 0.5 V_{DSS}$, $I_D = 0.5 I_{D25}$	150	nC	
		40	nC	
		80	nC	
R_{thJC}			0.25	°C/W
R_{thcs}	(TO-3P)	0.21		°C/W

Source-Drain Diode

Characteristic Values
($T_J = 25^\circ \text{C}$, unless otherwise specified)

Symbol	Test Conditions	Min.	Typ.	Max.
I_s	$V_{GS} = 0 \text{ V}$		120	A
I_{SM}	Repetitive		260	A
V_{SD}	$I_F = I_s$, $V_{GS} = 0 \text{ V}$, Pulse test, $t \leq 300 \mu\text{s}$, duty cycle $d \leq 2 \%$		1.5	V
t_{rr} Q_{RM}	$I_F = 25 \text{ A}$, $-di/dt = 100 \text{ A}/\mu\text{s}$ $V_R = 100 \text{ V}$, $V_{GS} = 0 \text{ V}$	150	ns	
		2.3	μC	

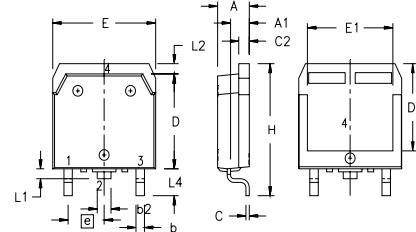
TO-3P (IXTQ) Outline



SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.185	.193	4.70	4.90
A1	.051	.059	1.30	1.50
A2	.057	.065	1.45	1.65
b	.035	.045	0.90	1.15
b2	.075	.087	1.90	2.20
b4	.114	.126	2.90	3.20
c	.022	.031	0.55	0.80
D	.780	.791	19.80	20.10
D1	.665	.677	16.90	17.20
E	.610	.622	15.50	15.80
E1	.531	.539	13.50	13.70
e	.215	BSC	5.45	BSC
L	.779	.795	19.80	20.20
L1	.134	.142	3.40	3.60
$\varnothing P$.126	.134	3.20	3.40
$\varnothing P1$.272	.280	6.90	7.10
S	.193	.201	4.90	5.10

All metal areas are tin plated.

TO-268 Outline

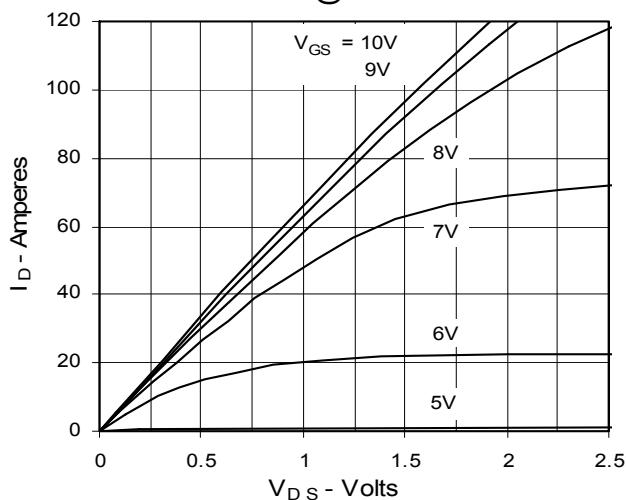


SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.193	.201	4.90	5.10
A1	.106	.114	2.70	2.90
A2	.001	.010	0.02	0.25
b	.045	.057	1.15	1.45
b2	.075	.083	1.90	2.10
C	.016	.026	0.40	0.65
C2	.057	.063	1.45	1.60
D	.543	.551	13.80	14.00
D1	.488	.500	12.40	12.70
E	.624	.632	15.85	16.05
E1	.524	.535	13.30	13.60
e	.215	BSC	5.45	BSC
H	.736	.752	18.70	19.10
L	.094	.106	2.40	2.70
L1	.047	.055	1.20	1.40
L2	.039	.045	1.00	1.15
L3	.010	BSC	0.25	BSC
L4	.150	.161	3.80	4.10

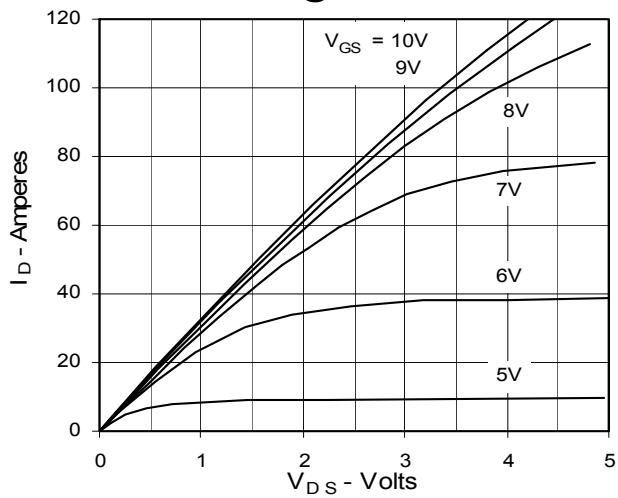
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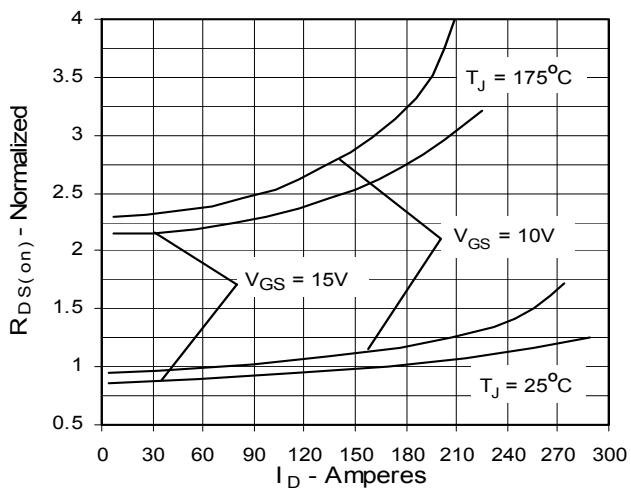
**Fig. 1. Output Characteristics
@ 25°C**



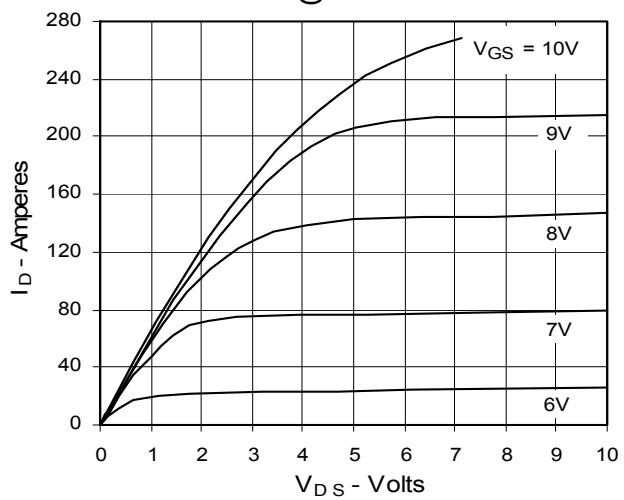
**Fig. 3. Output Characteristics
@ 150°C**



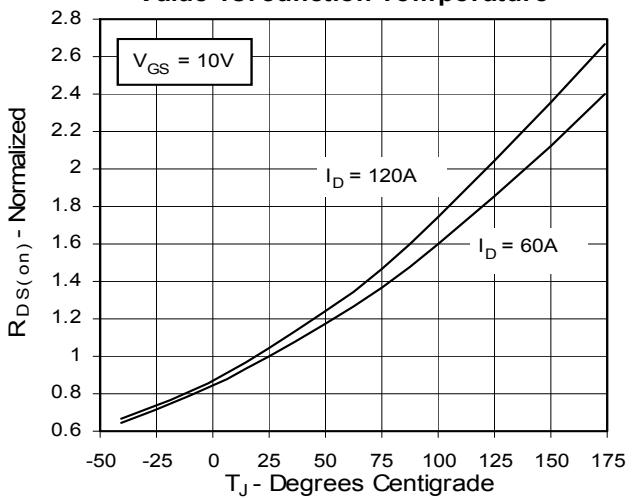
**Fig. 5. $R_{DS(on)}$ Normalized to 0.5 I_{D25}
Value vs. Drain Current**



**Fig. 2. Extended Output Characteristics
@ 25°C**



**Fig. 4. $R_{DS(on)}$ Normalized to 0.5 I_{D25}
Value vs. Junction Temperature**



**Fig. 6. Drain Current vs. Case
Temperature**

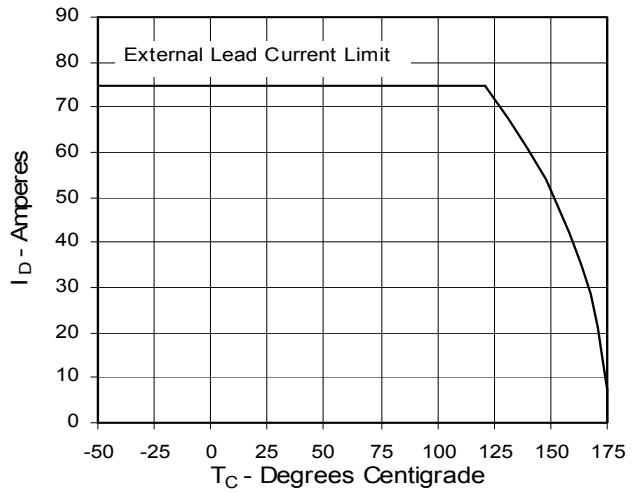


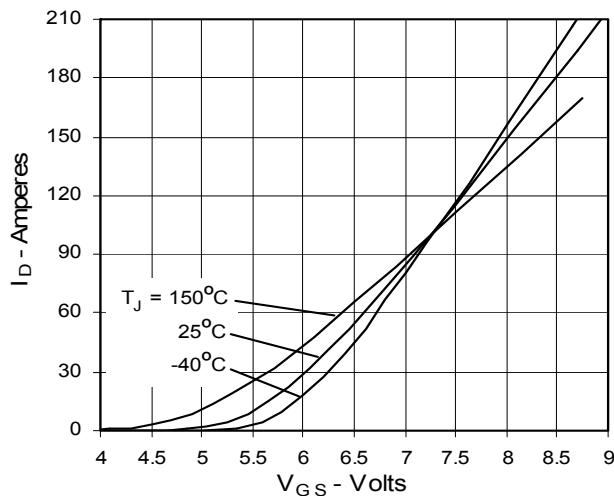
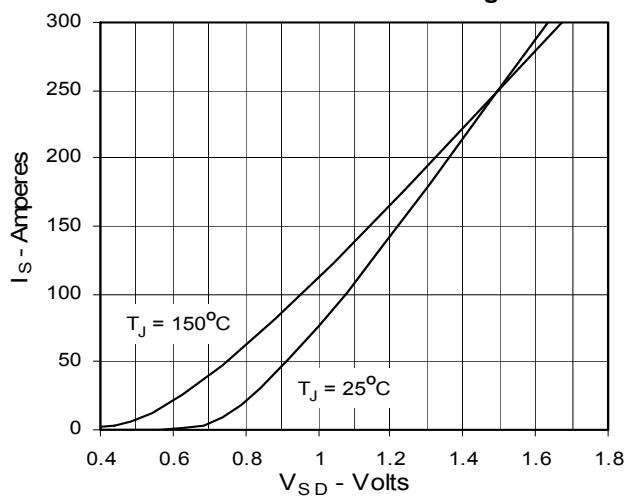
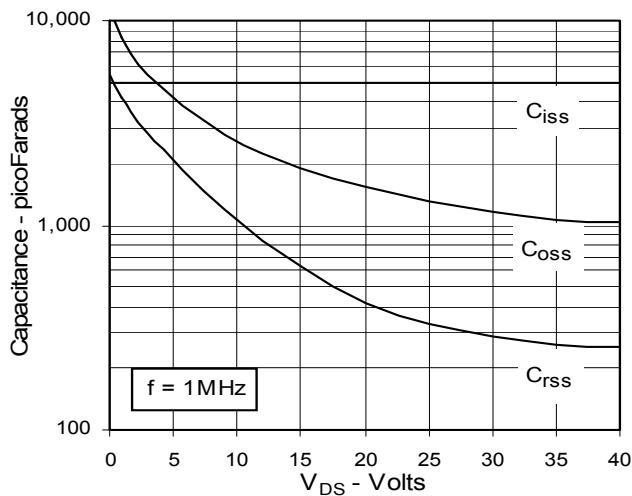
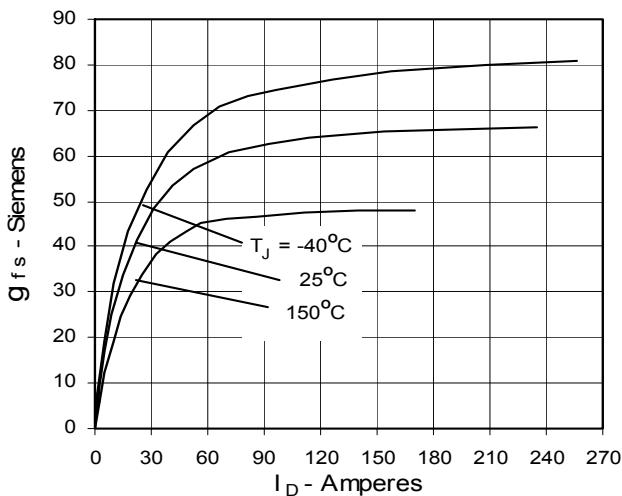
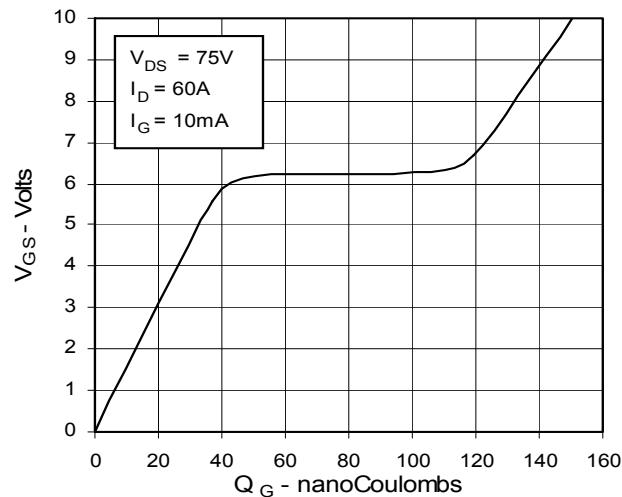
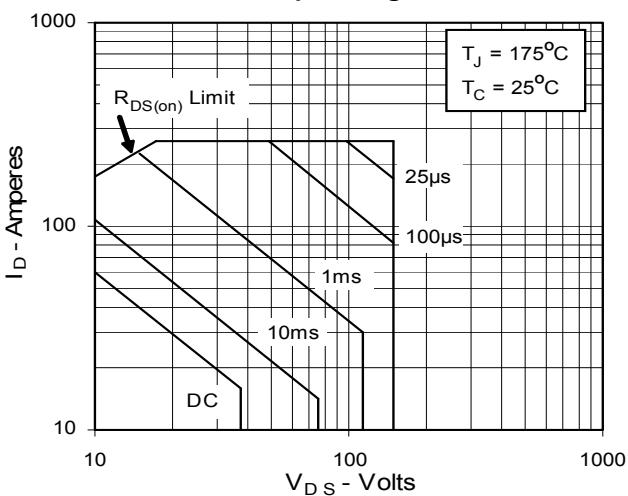
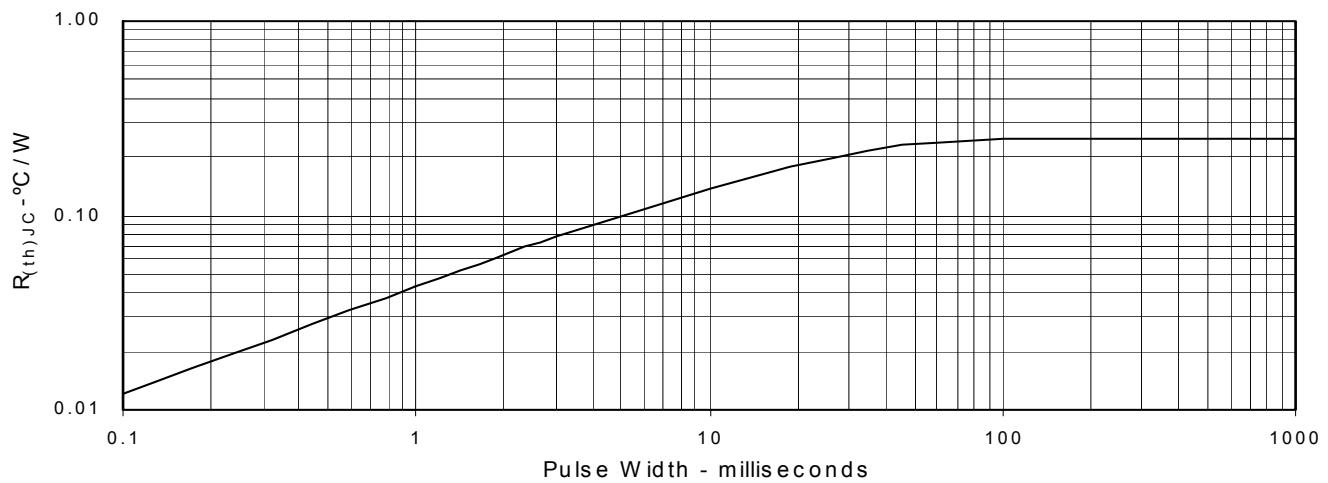
Fig. 7. Input Admittance**Fig. 9. Source Current vs. Source-To-Drain Voltage****Fig. 11. Capacitance****Fig. 8. Transconductance****Fig. 10. Gate Charge****Fig. 12. Forward-Bias Safe Operating Area**

Fig. 13. Maximum Transient Thermal Resistance

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